FIG. 1

100

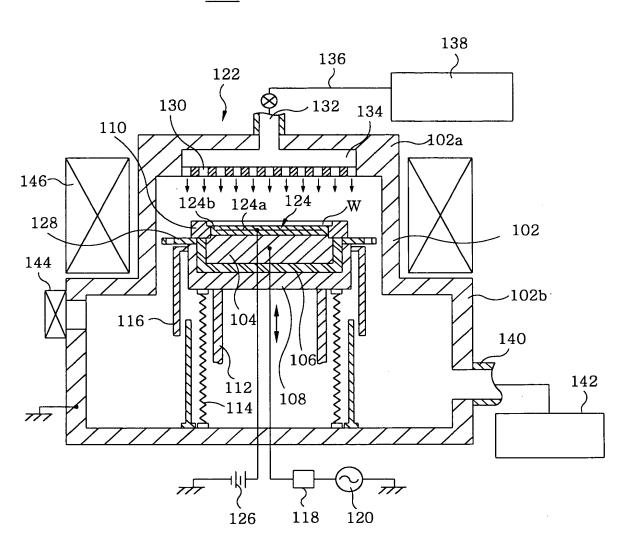


FIG.2A

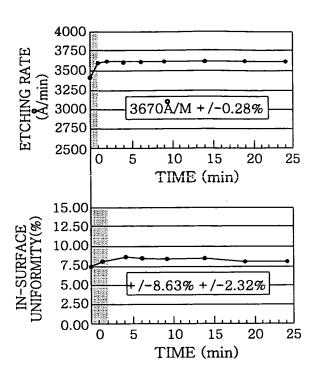


FIG.2B

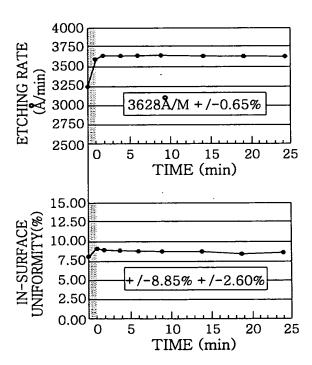


FIG.2C

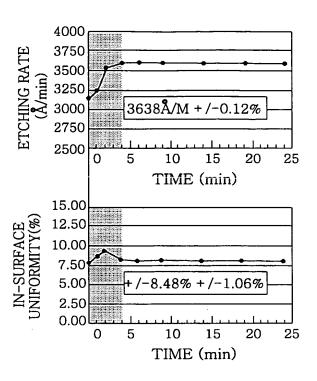


FIG.2D

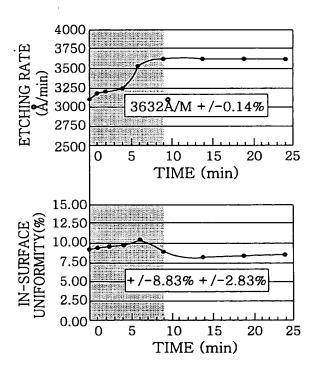
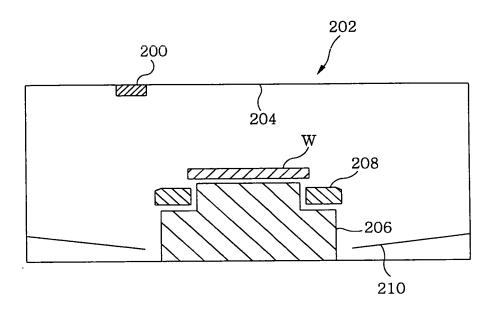


FIG.3



O(2s)O(2p)

(qS)iS.

XPS ANALYSIS RESULT OF SURFACE OF YZO3 CHIP SURFACE OF YZO3 CHIP O(128)

O(Auger)

O(Auger)

Si(SS)

Si(SS)

BINDING ENERGY(eV)

PHOTOELECTRON INTENSITY

FIG.5

XPS ANALYSIS RESULT OF

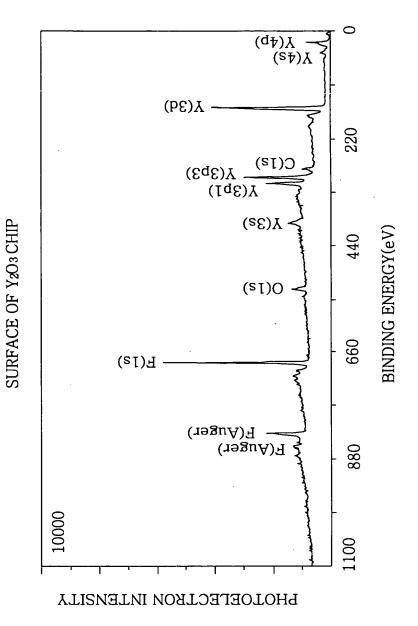


FIG.6

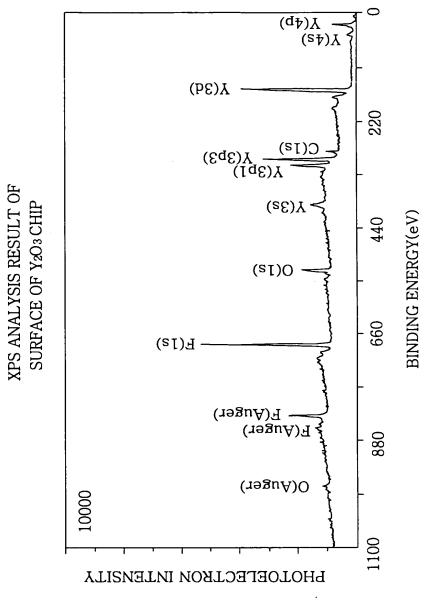


FIG. 7A

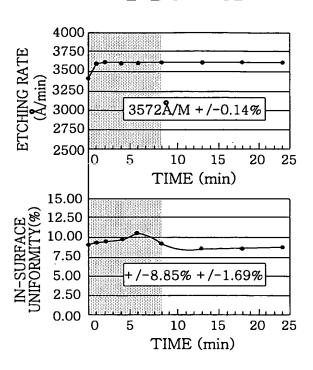
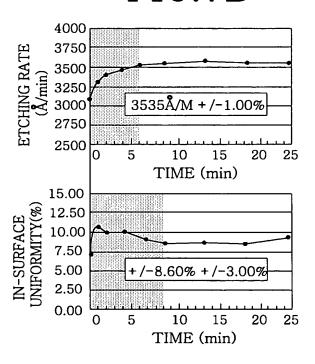


FIG.7B



OBLON, SPIVAK, ET AL DOCKET #: 245742US2 INV: Hiromi SAKIMA SHEET 9 OF 15

FIG.7C

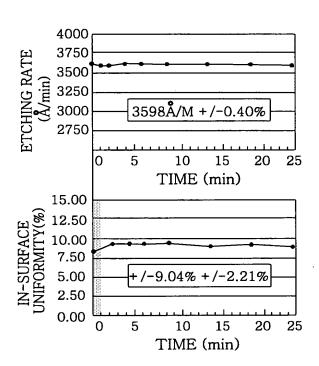


FIG.8A

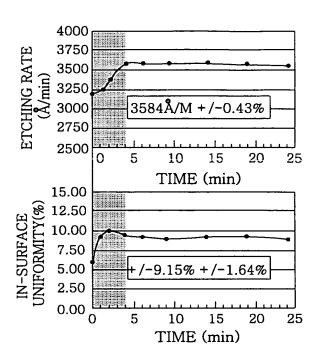


FIG.8B

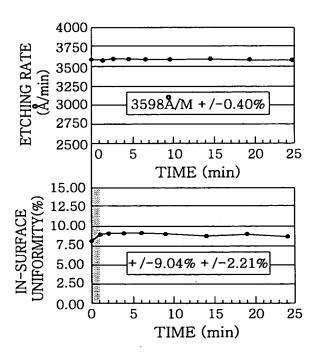


FIG.8C

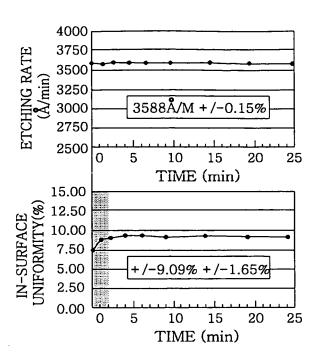


FIG.8D

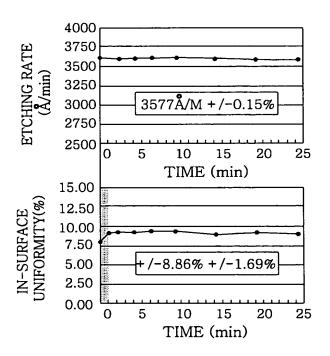


FIG.9

300

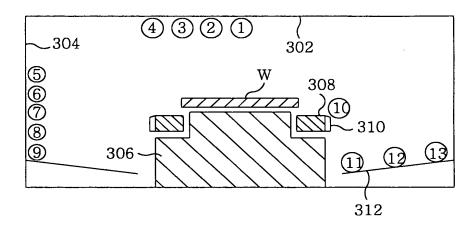


FIG. 10

	ASHING RATE (Å/min)		
CF4 FLOW RATE	0 sccm	2 sccm	
① CEILING PLATE 0mm(Center)	7877	7598	
②CEILING PLATE 50mm	8398	7976	
③CEILING PLATE 95mm	9304	9304 9136	
4 CEILING PLATE 140mm(Edge)	8994	9387	
5 DEPOSITION SHIELD 50mm(Top)	8674	7615	
6 DEPOSITION SHIELD 40mm	10540	9896	
⑦ DEPOSITION SHIELD 30mm	8849	8285	
® DEPOSITION SHIELD 20mm	10323	9696	
9 DEPOSITION SHIELD 10mm(Bot)	12260	12260 11907	
① INSULATOR RING	18295 1751		
① BAFFLE PLATE Center	9524	9016	
2 BAFFLE PLATE Middle	12012	11701	
3 BAFFLE PLATE Edge	12152 1150		
Max.	18295	17513	
Min.	7877	7598	
Ave.	10554	10095	
Unif.	49.36	49.11	

FIG. 11

	TIME REQUIRED TO REMOVE THE DEPOSIT (s)		
APPLIED POWER	500 W	1000 W	1500 W
① CEILING PLATE Omm(Center)	551	351	254
②CEILING PLATE 50mm	590	361	283
③CEILING PLATE 95mm	518	363	298
4 CEILING PLATE 140mm(Edge)	312	257	234
(5) DEPOSITION SHIELD 50mm(Top)	0	0	0
6 DEPOSITION SHIELD 40mm	0	0	0
⑦DEPOSITION SHIELD 30mm	26	20	17
® DEPOSITION SHIELD 20mm	146	113	95
9 DEPOSITION SHIELD 10mm(Bot)	243	167	140
(I) INSULATOR RING	0	0	0
① BAFFLE PLATE Center	0	0	0
②BAFFLE PLATE Middle	184	120	102
3 BAFFLE PLATE Edge	434	270	222
Max.	590	363	298
Min.	0	0	0
Ave.	231	156	127
Unif.	127.68	116.68	117.92

FIG. 12A

